

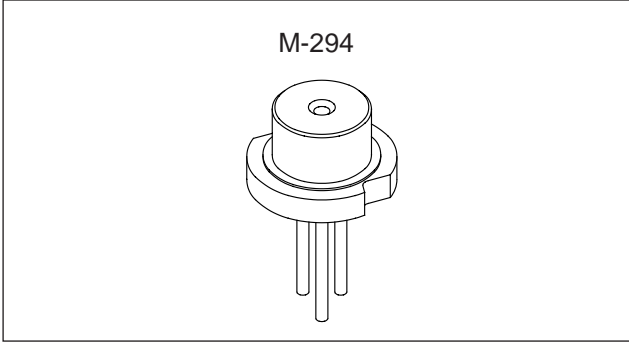
## 650nm Index-Guided Red Laser Diode

### Description

The SLD1135VS is a index-guided red laser diode for Laser pointer. The wavelength is 20nm shorter than SLD1122VS.

### Features

- Small astigmatism (7μm typ.)
- Small package (φ5.6mm)
- Single longitudinal mode
- Low operating voltage (2.5V Max)
- Max operating temperature = 40°C (Case temperature)



### Applications

Laser pointer

### Structure

- AlGaInP MQW laser diode
- PIN photodiode to monitor laser beam output

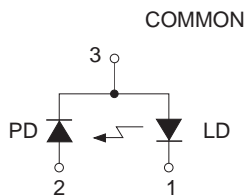
### Recommend Optical Power Output

5mW

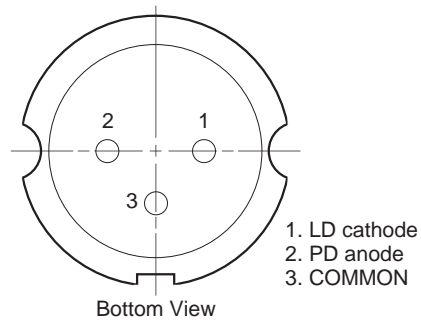
### Absolute Maximum Ratings (Tc = 25°C)

- |                         |                   |            |    |
|-------------------------|-------------------|------------|----|
| • Optical power output  | Po                | 5          | mW |
| • Reverse voltage       | V <sub>R</sub> LD | 2          | V  |
|                         | PD                | 15         | V  |
| • Operating temperature | T <sub>opr</sub>  | -10 to +40 | °C |
| • Storage temperature   | T <sub>stg</sub>  | -40 to +85 | °C |

### Connection Diagram



### Pin Configuration



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**Electrical and Optical Characteristics (Tc = 25°C)**

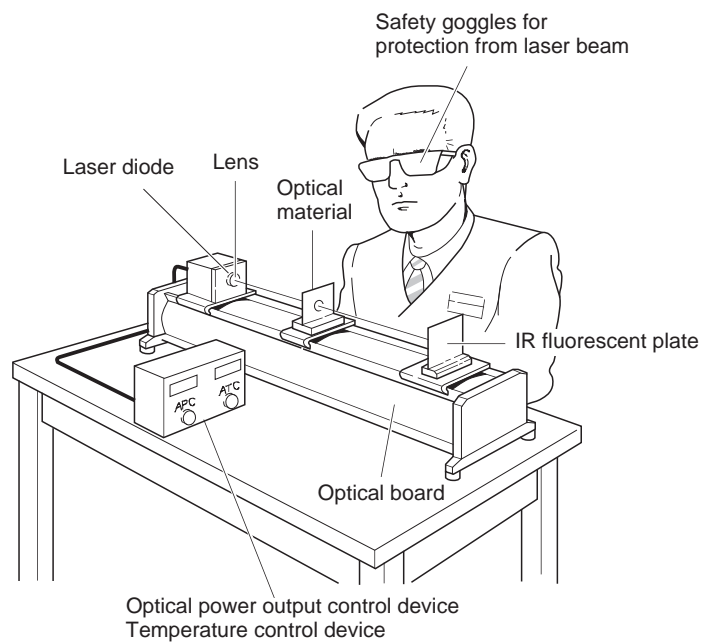
Tc: Case temperature

Item		Symbol	Conditions	Min.	Typ.	Max.	Unit	
Threshold current		I <sub>th</sub>			30	40	mA	
Operating current		I <sub>op</sub>	P <sub>o</sub> = 5mW		35	45	mA	
Operating voltage		V <sub>op</sub>	P <sub>o</sub> = 5mW		2.2	2.5	V	
Wavelength		λ <sub>p</sub>	P <sub>o</sub> = 5mW		650	660	nm	
Radiation angle	Perpendicular	θ <sub>⊥</sub>	P <sub>o</sub> = 5mW	22	30	40	degree	
	Parallel	θ <sub>//</sub>						5
Positional accuracy	Position	ΔX, ΔY, ΔZ	P <sub>o</sub> = 5mW			±150	μm	
	Angle	Δφ <sub>//</sub>					±3	degree
		Δφ <sub>⊥</sub>					±3	degree
Differential efficiency		η <sub>D</sub>	P <sub>o</sub> = 5mW	0.3	0.6	0.9	mW/mA	
Astigmatism		A <sub>s</sub>	P <sub>o</sub> = 5mW		7	15	μm	
Monitor current		I <sub>mon</sub>	P <sub>o</sub> = 5mW, V <sub>R</sub> = 5V	0.05	0.1	0.25	mA	

**Handling Precautions**

(1) Eye protection against laser beams

The optical output of laser diodes ranges from several mW to 4W. However the optical power density of the laser beam at the diode chip reaches 1MW/cm<sup>2</sup>. Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.



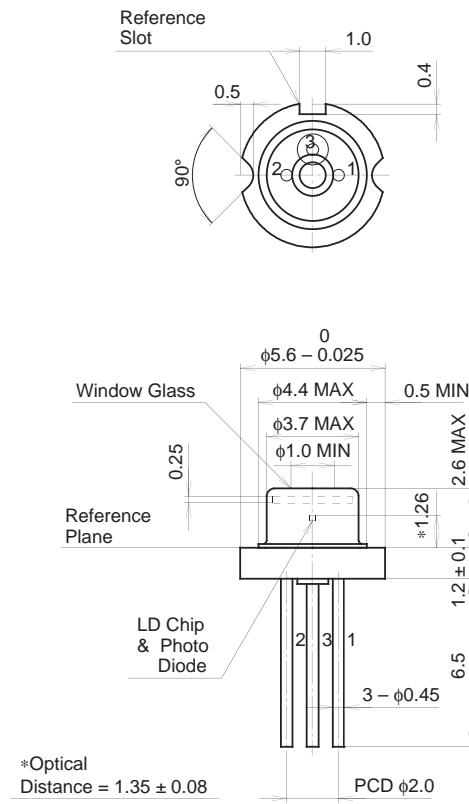
(2) Prevention of surge current and electrostatic discharge

Laser diode is most sensitive to electrostatic discharge among semiconductors. When a large current is passed through the laser diode even for an extremely short time (in the order of nanosecond), the strong light emitted from the laser diode promotes deterioration and then laser diodes are destroyed. Therefore, note that the surge current should not flow the laser diode driving circuit from switches and others. Also, if the laser diode is handled carelessly, it may be destructed instantly because electrostatic discharge is easily applied by a human body. Be great careful about excess current and electrostatic discharge.

Package Outline

Unit: mm

M-294



SONY CODE	M-294
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE WEIGHT	0.3g
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